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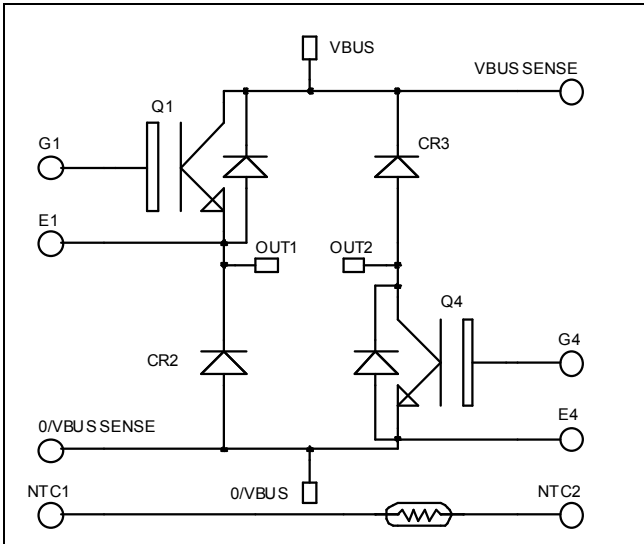
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**Asymmetrical - Bridge  
Trench + Field Stop IGBT3  
Power Module**

**$V_{CES} = 600V$   
 $I_C = 150A @ T_c = 80^\circ C$**

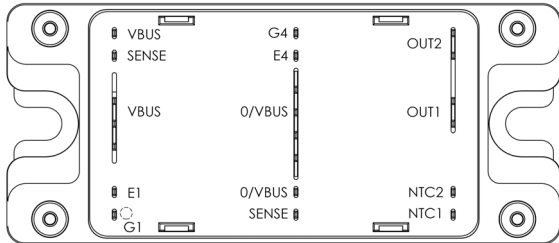


### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



### Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

### Absolute maximum ratings

| Symbol    | Parameter                             | Max ratings         | Unit        |
|-----------|---------------------------------------|---------------------|-------------|
| $V_{CES}$ | Collector - Emitter Breakdown Voltage | 600                 | V           |
| $I_C$     | Continuous Collector Current          | $T_c = 25^\circ C$  | 225         |
|           |                                       | $T_c = 80^\circ C$  | 150         |
| $I_{CM}$  | Pulsed Collector Current              | $T_c = 25^\circ C$  | 350         |
| $V_{GE}$  | Gate - Emitter Voltage                | $\pm 20$            | V           |
| $P_D$     | Maximum Power Dissipation             | $T_c = 25^\circ C$  | 480         |
| RBSOA     | Reverse Bias Safe Operating Area      | $T_j = 150^\circ C$ | 300A @ 550V |

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

| Symbol        | Characteristic                       | Test Conditions                               | Min | Typ        | Max | Unit          |
|---------------|--------------------------------------|---|-----|------------|-----|---------------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0\text{V}$ , $V_{CE} = 600\text{V}$ |     |            | 250 | $\mu\text{A}$ |
| $V_{CE(sat)}$ | Collector Emitter Saturation Voltage | $V_{GE} = 15\text{V}$<br>$I_C = 150\text{A}$  |     | 1.5<br>1.7 | 1.9 | V             |
| $V_{GE(th)}$  | Gate Threshold Voltage               | $V_{GE} = V_{CE}$ , $I_C = 1.5\text{ mA}$     | 5.0 | 5.8        | 6.5 | V             |
| $I_{GES}$     | Gate – Emitter Leakage Current       | $V_{GE} = 20\text{V}$ , $V_{CE} = 0\text{V}$  |     |            | 400 | nA            |

**Dynamic Characteristics**

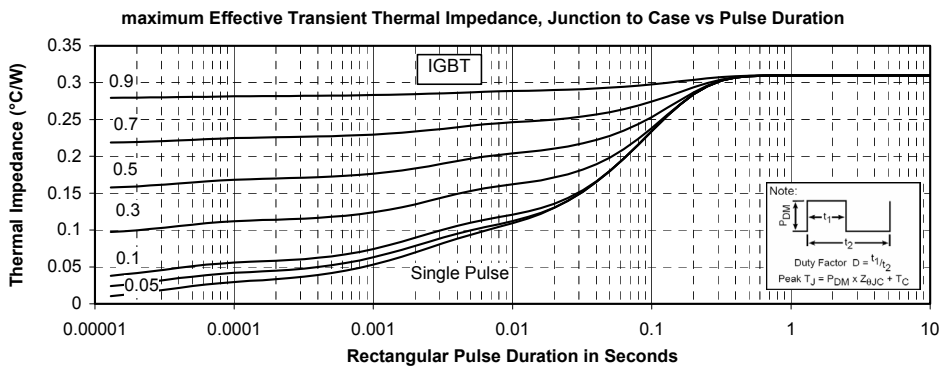
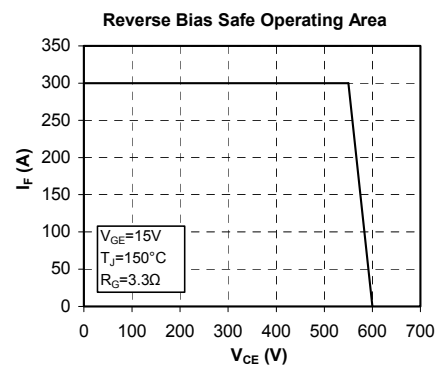
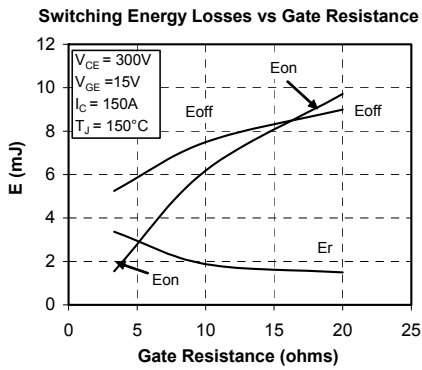
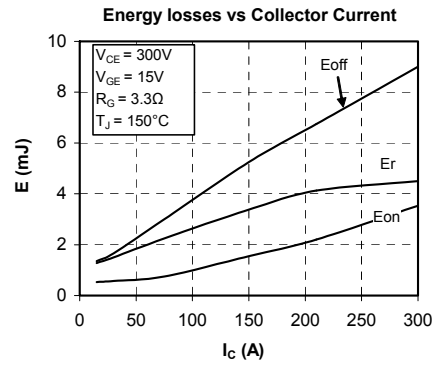
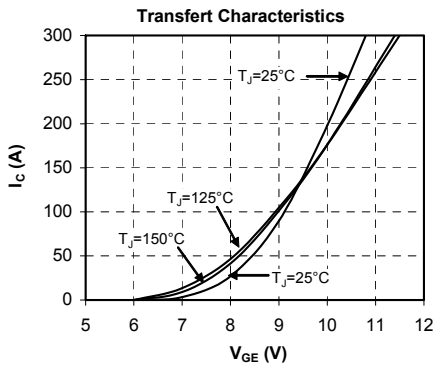
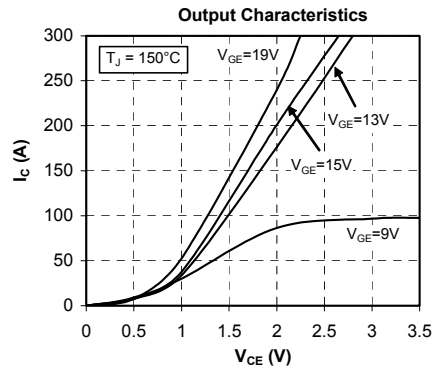
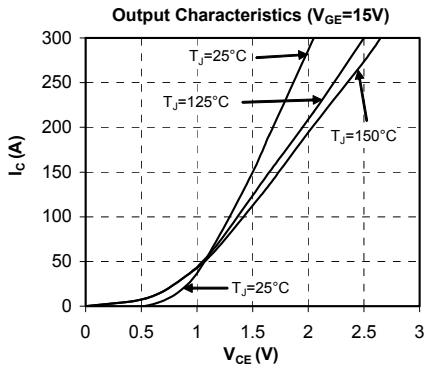
| Symbol       | Characteristic               | Test Conditions   | Min                       | Typ  | Max | Unit |
|--------------|------------------------------|---|---------------------------|------|-----|------|
| $C_{ies}$    | Input Capacitance            | $V_{GE} = 0\text{V}$  |                           | 9200 |     | pF   |
| $C_{oes}$    | Output Capacitance           | $V_{CE} = 25\text{V}$   |                           | 580  |     |      |
| $C_{res}$    | Reverse Transfer Capacitance | $f = 1\text{MHz}$   |                           | 270  |     |      |
| $T_{d(on)}$  | Turn-on Delay Time           | Inductive Switching ( $25^\circ\text{C}$ )                                  |                           | 115  |     | ns   |
| $T_r$        | Rise Time                    | $V_{GE} = \pm 15\text{V}$   |                           | 45   |     |      |
| $T_{d(off)}$ | Turn-off Delay Time          | $V_{Bus} = 300\text{V}$<br>$I_C = 150\text{A}$                              |                           | 225  |     |      |
| $T_f$        | Fall Time                    | $R_G = 3.3\Omega$   |                           | 55   |     |      |
| $T_{d(on)}$  | Turn-on Delay Time           | Inductive Switching ( $150^\circ\text{C}$ )                                 |                           | 130  |     | ns   |
| $T_r$        | Rise Time                    | $V_{GE} = \pm 15\text{V}$   |                           | 50   |     |      |
| $T_{d(off)}$ | Turn-off Delay Time          | $V_{Bus} = 300\text{V}$<br>$I_C = 150\text{A}$                              |                           | 300  |     |      |
| $T_f$        | Fall Time                    | $R_G = 3.3\Omega$   |                           | 70   |     |      |
| $E_{on}$     | Turn on Energy               | $V_{GE} = \pm 15\text{V}$<br>$V_{Bus} = 300\text{V}$<br>$I_C = 150\text{A}$ | $T_j = 25^\circ\text{C}$  | 0.85 |     | mJ   |
| $E_{off}$    | Turn off Energy              | $R_G = 3.3\Omega$   | $T_j = 150^\circ\text{C}$ | 1.5  |     | mJ   |
|              |                              |   | $T_j = 25^\circ\text{C}$  | 4.1  |     | mJ   |
|              |                              |   | $T_j = 150^\circ\text{C}$ | 5.3  |     | mJ   |

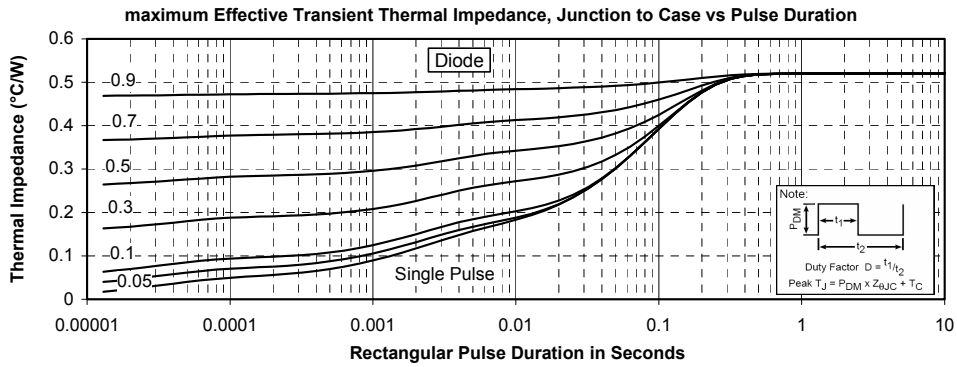
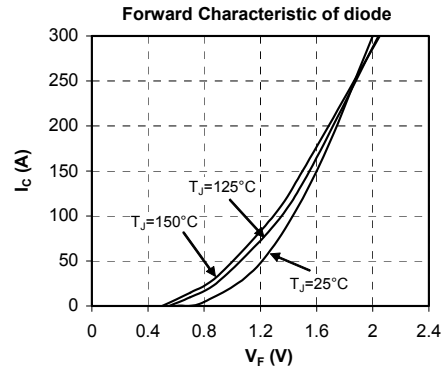
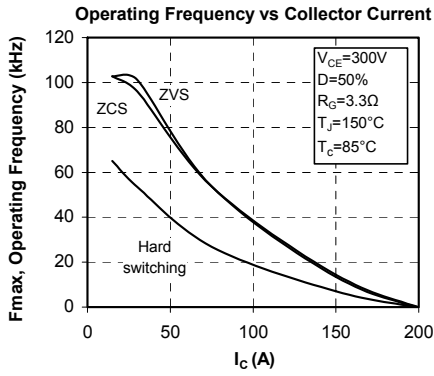
**Reverse diode ratings and characteristics**

| Symbol    | Characteristic                          | Test Conditions  | Min   | Typ         | Max        | Unit          |
|-----------|---|--|---|-------------|------------|---------------|
| $V_{RRM}$ | Maximum Peak Repetitive Reverse Voltage |  | 600   |             |            | V             |
| $I_{RM}$  | Maximum Reverse Leakage Current         | $V_R = 600\text{V}$  |   |             | 250<br>500 | $\mu\text{A}$ |
| $I_F$     | DC Forward Current                      |  |   | 150         |            | A             |
| $V_F$     | Diode Forward Voltage                   | $I_F = 150\text{A}$<br>$V_{GE} = 0\text{V}$                                      | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ | 1.6<br>1.5  | 2          | V             |
| $t_{rr}$  | Reverse Recovery Time                   |  | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ | 130<br>225  |            | ns            |
| $Q_{rr}$  | Reverse Recovery Charge                 | $I_F = 150\text{A}$<br>$V_R = 300\text{V}$<br>$di/dt = 3000\text{A}/\mu\text{s}$ | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ | 6.9<br>14.5 |            | $\mu\text{C}$ |
| $E_r$     | Reverse Recovery Energy                 |  | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ | 1.6<br>3.5  |            | mJ            |



## Typical Performance Curve





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